

Listing of claims:

1. (Currently Amended) An apparatus comprising:
a first wafer;
a second wafer; and
a conductive rim between the first and second wafers, the conductive rim electrically and mechanically connecting the first and second wafers, the conductive rim and second wafer at least in part sealing an area on the surface of the first wafer,
wherein the conductive rim and second wafer hermetically seal the area on the surface of the first wafer.
2. (Cancelled)
3. (Original) The apparatus as defined by claim 1 wherein the conductive rim comprises a silicide.
4. (Original) The apparatus as defined by claim 1 wherein the area on the first wafer includes MEMS structure.
5. (Original) The apparatus as defined by claim 4 wherein the conductive rim is electrically isolated from the MEMS structure.
6. (Original) The apparatus as defined by claim 4 wherein the second wafer includes a cap.
7. (Original) The apparatus as defined by claim 1 wherein the first wafer includes circuitry capable of delivering a bias voltage to the second wafer via the conductive rim.

8. (Original) The apparatus as defined by claim 7 wherein the circuitry has a maximum temperature to which it can be exposed, the conductive rim being produced from a material that interdiffuses or melts at a temperature that is less than the maximum temperature to which the circuitry can be exposed.
9. (Original) The apparatus as defined by claim 1 wherein at least one of the first wafer and the second wafer comprises a silicon based material.
10. (Original) The apparatus as defined by claim 1 wherein at least one of the first wafer and the second wafer is comprised of polysilicon, single crystal silicon, or silicon germanium.
11. (Currently Amended) A MEMS device comprising:
 - a first wafer;
 - a second wafer; and
 - conductive and sealing means between the first and second wafers, the conductive and sealing means electrically and mechanically connecting the first and second wafers, the second wafer and the conductive and sealing means at least in part sealing an area on the surface of the first wafer

wherein the area on the first wafer includes a MEMS structure.
12. (Original) The MEMS device as defined by claim 11 wherein the conductive and sealing means includes a silicide bond between the first and second wafers.
13. (Original) The MEMS device as defined by claim 11 further including means for applying a bias voltage to the second wafer through the conductive and sealing means, the applying means being on the first wafer.

Claims 14-20 (Cancelled)

21. (New) An apparatus comprising:
 - a first wafer;
 - a second wafer; and
 - a conductive rim between the first and second wafers, the conductive rim electrically and mechanically connecting the first and second wafers, the conductive rim and second wafer at least in part sealing an area on the surface of the first wafer, wherein the area on the first wafer includes MEMS structure.
22. (New) The apparatus as defined by claim 21 wherein the conductive rim comprises a silicide.
23. (New) The apparatus as defined by claim 21 wherein the conductive rim is electrically isolated from the MEMS structure.
24. (New) The apparatus as defined by claim 21 wherein the second wafer includes a cap.
25. (New) The apparatus as defined by claim 21 wherein the first wafer includes circuitry capable of delivering a bias voltage to the second wafer via the conductive rim.
26. (New) The apparatus as defined by claim 25 wherein the circuitry has a maximum temperature to which it can be exposed, the conductive rim being produced from a material that interdiffuses or melts at a temperature that is less than the maximum temperature to which the circuitry can be exposed.